

SOT-23 Plastic-Encapsulate Transistors

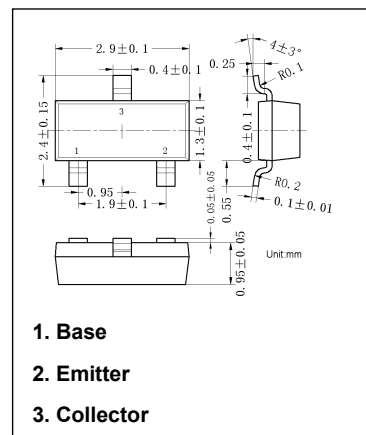
BC857C PNP Transistors

Features

- Ideally suited for automatic insertion
- For switching and AF amplifier applications

Marking

- BC857A: 3E
- BC857B: 3F
- BC857C: 3G



Maximum Ratings (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector Base Voltage	-50	V
V _{CEO}	Collector Emitter Voltage	-45	V
V _{EBO}	Emitter Base Voltage	-5	V
I _c	Collector Current	-0.1	A
P _c	Collector Power Dissipation	200	mW
R _{θJA}	Thermal Resistance from Junction to Ambient	625	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	- 55 to +150	°C

Electrical Characteristics (T_a=25°C unless otherwise specified)

Symbol	Parameter	Test Conditions		Min	Typ	Max	Unit
V _{(BR)CBO}	Collector-base breakdown voltage	I _C = -10μA, I _E = 0		-50			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C = -10mA, I _B = 0		-45			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E = -1μA, I _C = 0		-5			V
I _{CBO}	Collector cut-off current	V _{CB} = -45V, I _E = 0				-100	nA
I _{CEO}	Collector cut-off current	V _{CE} = -40V, I _B = 0				-100	nA
I _{EBO}	Emitter cut-off current	V _{EB} = -5V, I _C = 0				-100	nA
h _{FE}	DC current gain	BC857A	V _{CE} = -5V, I _C = -2mA	125	210	250	
		BC857B		220	310	475	
		BC857C		420	520	800	
		V _{CE} = -5V, I _C = -1mA		125			
V _{CE(sat)}	Collector-emitter saturation voltage	I _C = -100mA, I _B = -5mA				-0.5	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C = -100mA, I _B = -5mA				-1.1	V
f _T	Transition frequency	V _{CE} = -5V, I _C = -10mA, f = 100MHz		100			MHz
C _{ob}	Collector output capacitance	V _{CB} = -10V, f = 1MHz				4.5	pF

Typical Characteristics

